

Title (en)
SEMICONDUCTOR MEMORY WITH MEMORY CELLS COMPRISING A VERTICAL SELECTION TRANSISTOR AND METHOD FOR PRODUCTION THEREOF

Title (de)
HALBLEITERSPEICHER MIT EINEN VERTIKALEN AUSWAHLTRANSISTOR UMFASSENDEN SPEICHERZELLEN SOWIE VERFAHREN ZU SEINER HERSTELLUNG

Title (fr)
MEMOIRE A SEMI-CONDUCTEUR A CELLULES DE MEMOIRE COMPORTANT UN TRANSISTOR DE SELECTION VERTICAL, ET PROCEDE PERMETTANT DE LA PRODUIRE

Publication
EP 1423874 A2 20040602 (DE)

Application
EP 02764546 A 20020814

Priority
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• DE 10143650 A 20010905

Abstract (en)
[origin: DE10143650A1] A semiconductor memory cell has trenches (25,50) in a substrate (15) having a capacitor (30) and long trenches having spacer wordlines with an active region between them having a vertical select transistor. Conductive bridges between wordlines in a trench are less than half as thick as the trench width. An Independent claim is also included for a process for making the above memory.

IPC 1-7
H01L 21/8242

IPC 8 full level
H01L 21/8242 (2006.01); **H01L 27/108** (2006.01)

CPC (source: EP KR US)
H10B 12/00 (2023.02 - KR); **H10B 12/0383** (2023.02 - EP US); **H10B 12/395** (2023.02 - EP US); **H10B 12/488** (2023.02 - EP US); **H10B 12/0385** (2023.02 - EP US)

Citation (search report)
See references of WO 03028104A2

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DOCDB simple family (publication)
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